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FDP8030L/FDB8030L

N-Channel Logic Level PowerTrench® MOSFET

General Description

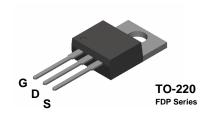
This N-Channel Logic level MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

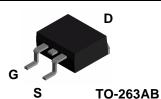
These MOSFETS feature faster switching and lower gate charge than other MOSFETS with comparable $R_{\text{DS}(\text{on})}$ specifications.

The result is a MOSFET that is easy and safer to drive (even at very high frequencies), and DC/DC power supply designs with higher overall efficiency.

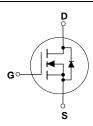
Features

- 80 A, 30 V. $R_{DS(ON)} = 0.0035 \ \Omega \ @ \ V_{GS} = 10 \ V$ $R_{DS(ON)} = 0.0045 \ \Omega \ @ \ V_{GS} = 4.5 \ V$
- Critical DC electrical parameters specified at elevated temperature
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor
- High performance trench technology for extremely low Rescont
- 175°C maximum junction temperature rating





FDB Series



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V _{DSS}	Drain-Source Voltage	30	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current - Continuous (Note 1)	80	А
	- Pulsed (Note 1)	300	
P _D	Total Power Dissipation @ T _C = 25°C	187	W
	Derate above 25°C	1.25	W°C
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-65 to +175	°C
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	275	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.8	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	°C/W

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Drain-Sc	ource Avalanche Ratings (Note	1)				•
W _{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 20 \text{ V}, \qquad I_D = 80 \text{ A}$			1500	mJ
I _{AR}	Maximum Drain-Source Avalanche Current				80	Α
Off Char	acteristics	_				
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	30			V
ΔBV _{DSS} ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$, Referenced to 25°C		23		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \text{ V}, \qquad V_{GS} = 0 \text{ V}$			10	μΑ
I _{GSSF}	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1	1.5	2	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C		- 5		mV/°C
R _{DS(on)}	Static Drain–Source On–Resistance	$V_{GS} = 10 \text{ V}, \qquad I_{D} = 80 \text{ A} $ $T_{J} = 125 ^{\circ}\text{C}$		3.1 4.0	3.5 5.6	mΩ
		$V_{GS} = 4.5 \text{ V}, \qquad I_{D} = 70 \text{ A}$		3.6	4.5	
$I_{D(on)}$	On–State Drain Current	$V_{GS} = 10 \text{ V}, \qquad V_{DS} = 10 \text{ V}$	60			Α
g FS	Forward Transconductance	$V_{DS} = 10 \text{ V}, \qquad I_{D} = 80 \text{ A}$		170		S
Dynamic	: Characteristics					
Ciss	Input Capacitance	$V_{DS} = 15 \text{ V}, \qquad V_{GS} = 0 \text{ V},$		10500		pF
Coss	Output Capacitance	f = 1.0 MHz		2700		pF
C _{rss}	Reverse Transfer Capacitance			1650		pF
Switchin	g Characteristics (Note 2)					
t _{D(on)}	Turn-On Delay Time	$V_{DD} = 15 \text{ V}, \qquad I_D = 50 \text{ A},$		20	35	ns
t _r	Turn-On Rise Time	$V_{GS} = 4.5 \text{ V}, \qquad R_{GEN} = 10 \Omega$		185	225	ns
t _{D (off)}	Turn-Off Delay Time	$R_{GS} = 10 \Omega$		160	200	ns
t _f	Turn-Off Fall Time	1		200	240	ns
Q _g	Total Gate Charge	V _{DS} = 15 V,		120	170	nC
Q_{gs}	Gate-Source Charge	$I_D = 80 \text{ A}, V_{GS} = 5 \text{ V}$		27		nC
Q_{gd}	Gate-Drain Charge			48		nC
Drain-S	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source				80	Α
I _{SM}	Maximum Pulsed Drain-Source Diode	e Forward Current (Note 1)			300	Α
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 80 \text{ A} \text{ (Note 1)}$		1	1.3	V

Notes:

^{1.} Pulse Test: Pulse Width < $300\mu s,$ Duty Cycle < 2.0%

Typical Characteristics

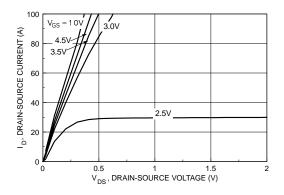
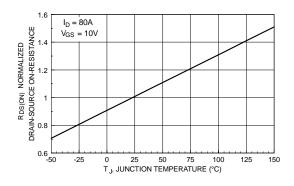


Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.



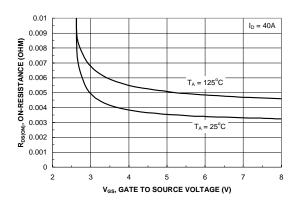
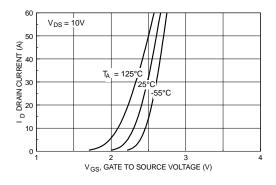


Figure 3. On-Resistance Variation with Temperature.

Figure 4. On-Resistance Variation with Gate-to-Source Voltage.



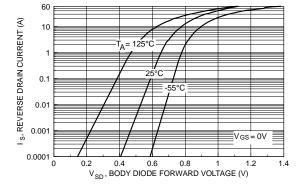
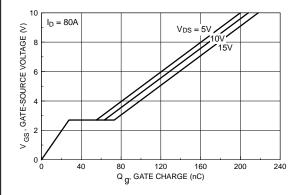


Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

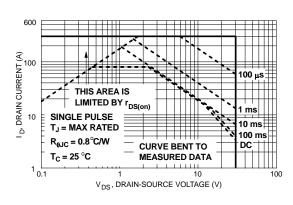
Typical Characteristics



18000 10000 10000 10000 10000 V_{GS} = 0V 10000 V_{DS}, DRAIN TO SOURCE VOLTAGE (V)

Figure 7. Gate Charge Characteristics.





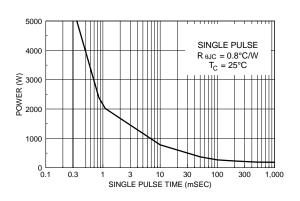


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

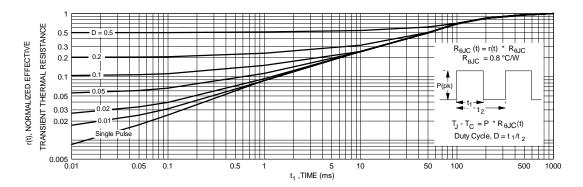


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.





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